#### MICONDUCTOR 201 COMPLIANCE **TO-220 ITO-220**

TO-252

(DPAK)

TAIWAN

**Pin Definition:** 

- 1. Gate 2. Drain
- 3. Source

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
900	5.1 @ V <sub>GS</sub> =10V	1.25

#### **General Description**

The TSM3N90 N-Channel Power MOSFET is produced by new advance planar process. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

ock Diagram

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#### **Features**

TO-251

(IPAK)

- Low R<sub>DS(ON)</sub> 4.3Ω (Typ.)
- Low gate charge typical @ 17nC (Typ.)

<ul> <li>Low Crss typical @ 8.7pF (Typ.)</li> </ul>					Ĺ
	Ordering Informati	on			
	Part No.	Package	Packing		
	TSM3N90CH C5G	TO-251	75pcs / Tube		
	TSM3N90CP ROG	TO-252	2.5Kpcs / 13" Reel	P	6
	TSM3N90CZ C0G	TO-220	50pcs / Tube		S
	TSM3N90CI C0G	ITO-220	50pcs / Tube		N-Channel MOSFET
	Natas "O" damataa fan Ll				

Note: "G" denotes for Halogen Free

#### Absolute Maximum Rating (Ta 25°C unless otherwise noted)

Parameter		Symbol	Limit			L Incit
			IPAK/DPAK	ITO-220	TO-220	Unit
Drain-Source Voltage		V <sub>DS</sub>	900			V
Gate-Source Voltage		V <sub>GS</sub>	±30			V
Continuous Drain Current	Tc = 25°C	- I <sub>D</sub> -	2.5			Α
	Tc = 100°C			А		
Pulsed Drain Current *		I <sub>DM</sub>	10			А
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	10			mJ
Avalanche Current (Repetitive) (Note 1)		I <sub>AR</sub>	2.5			А
Repetitive Avalanche Energy (Note 1)		E <sub>AR</sub>	9.4			mJ
Peak Diode Recovery dv/dt (Note 3)		dv/dt	4.5			V/ns
Total Power Dissipation @ $T_c = 25^{\circ}C$		P <sub>TOT</sub>	94	32	94	W
Operating Junction Temperature		TJ	150			°C
Storage Temperature Range		T <sub>STG</sub>	-55 to +150			°C
Note: Limited by maximum junct	ion temperature	•				•

Note: Limited by maximum junction temperature

# **TSM3N90**

900V N-Channel Power MOSFET



#### **Thermal Performance**

Parameter	Symbol	IPAK/DPAK	ITO-220	TO-220	Unit	
Thermal Resistance - Junction to Case	$R\Theta_{JC}$	1.33	1.33	3.9	°0.00	
Thermal Resistance - Junction to Ambient	RƏ <sub>JA</sub>	110	62	2.5	°C/W	

#### **Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250uA$	BV <sub>DSS</sub>	900		-	V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.25A$	R <sub>DS(ON)</sub>		4.3	5.1	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 uA$	V <sub>GS(TH)</sub>	2.0		4.0	V
Zero Gate Voltage Drain Current	$V_{DS} = 900V, V_{GS} = 0V$	I <sub>DSS</sub>			10	uA
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Forward Transfer Conductance	$V_{DS} = 30V, I_D = 1.25A$	<b>g</b> <sub>fs</sub>		3		S
Dynamic	·					
Total Gate Charge		Qg		17		nC
Gate-Source Charge	$V_{DS} = 720V, I_D = 2.5A,$	Q <sub>gs</sub>		2.4		
Gate-Drain Charge	$-V_{GS} = 10V$	Q <sub>gd</sub>		6.6		
Input Capacitance		C <sub>iss</sub>		748		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C <sub>oss</sub>		55		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		8.7		
Switching						
Turn-On Delay Time		t <sub>d(on)</sub>		16		
Turn-On Rise Time	$V_{GS} = 10V, I_D = 2.5A,$	t <sub>r</sub>		25		nS
Turn-Off Delay Time	$V_{DD} = 450V, R_{G} = 25\Omega$	t <sub>d(off)</sub>		63		113
Turn-Off Fall Time		t <sub>f</sub>		31		
Source-Drain Diode Ratings and	Characteristic	<u>.</u>				
Source Current	Integral reverse diode in	I <sub>S</sub>			2.5	Α
Source Current (Pulse)	the MOSFET	I <sub>SM</sub>			10	Α
Diode Forward Voltage	$I_{S} = 2.5A, V_{GS} = 0V$	V <sub>SD</sub>			1.5	V
Reverse Recovery Time	$V_{GS} = 0V, I_{S} = 2.5A,$	t <sub>fr</sub>		355		nS
Reverse Recovery Charge	dI <sub>F</sub> /dt = 100A/us	Q <sub>fr</sub>		1.8		uC

Note 1: Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

**Note 2:** Max Rating  $E_{AS}$  Test Condition:  $V_{DD} = 50V$ ,  $I_{AS}=2A$ , L=5mH,  $R_G=25\Omega$ , Starting  $T_J=25^{\circ}C$ 

Guaranteed 100%  $E_{AS}$  Test Condition:  $V_{DD}$  = 50V,  $I_{AS}$ =2A, L=1mH,  $R_G$  =25 $\Omega$ , Starting  $T_J$ =25°C

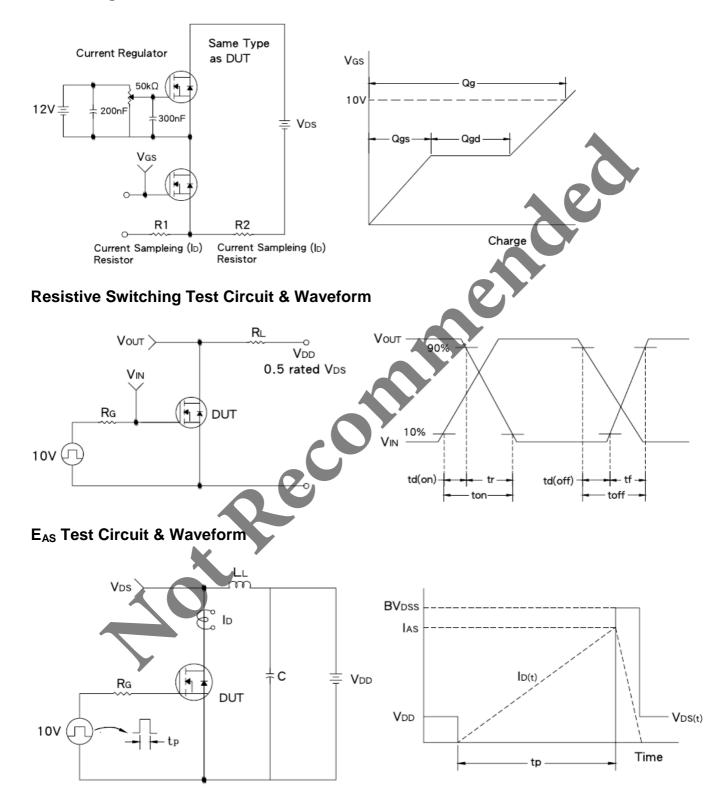
Note 3:  $I_{SD}\leq 2.5A$ , di/dt $\leq 200A/uS$ ,  $V_{DD}\leq BV_{DSS}$ , Starting  $T_J=25^{\circ}C$ 

Note 4: Pulse test: pulse width ≤300uS, duty cycle ≤2%

**Note 5:** Essentially Independent of Operating Temperature

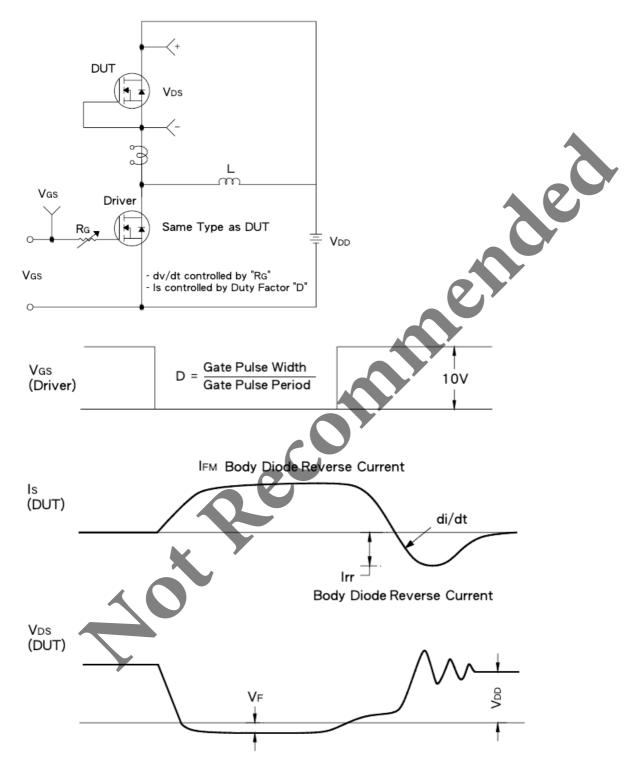


#### Gate Charge Test Circuit & Waveform



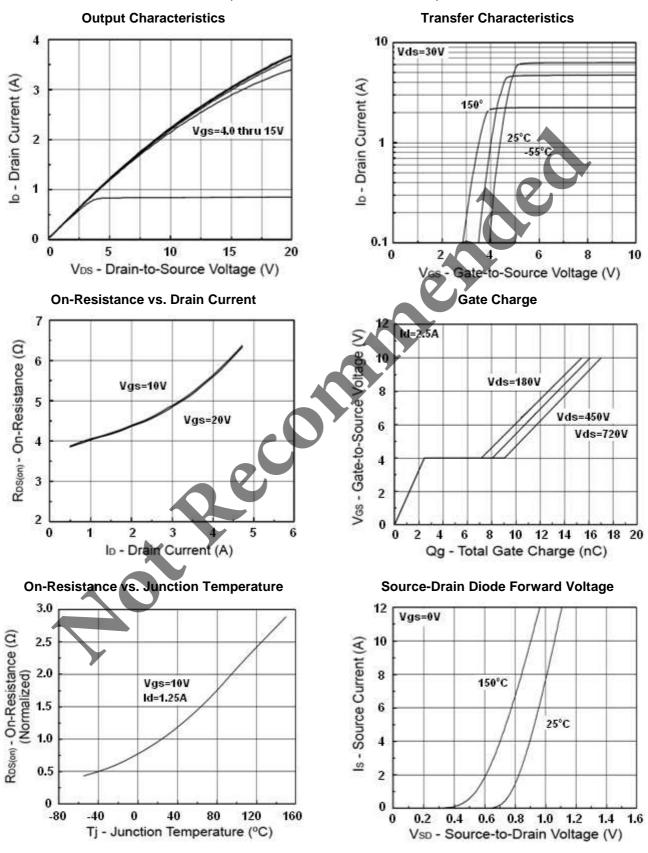


#### Diode Reverse Recovery Time Test Circuit & Waveform



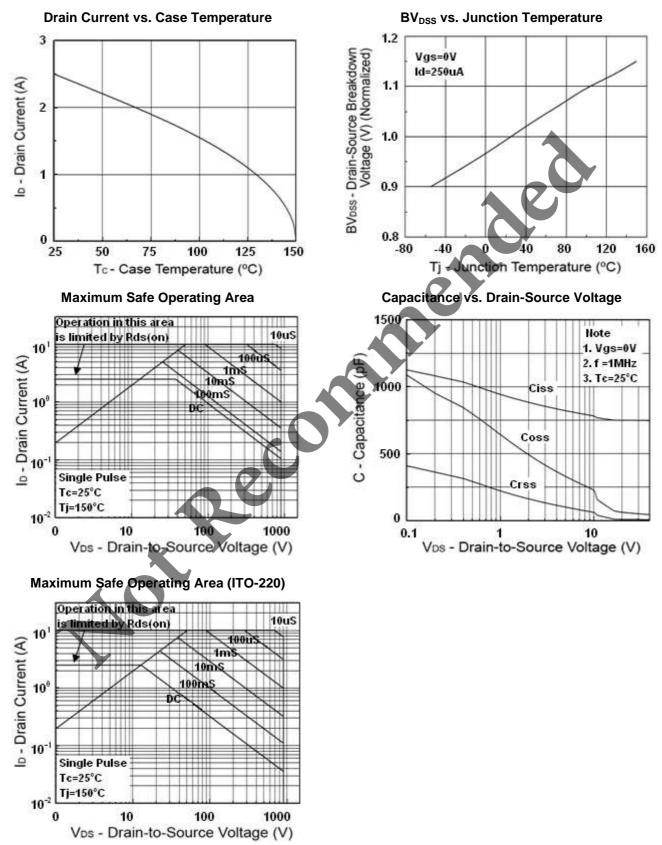


#### Electrical Characteristics Curve (Tc = 25°C, unless otherwise noted)



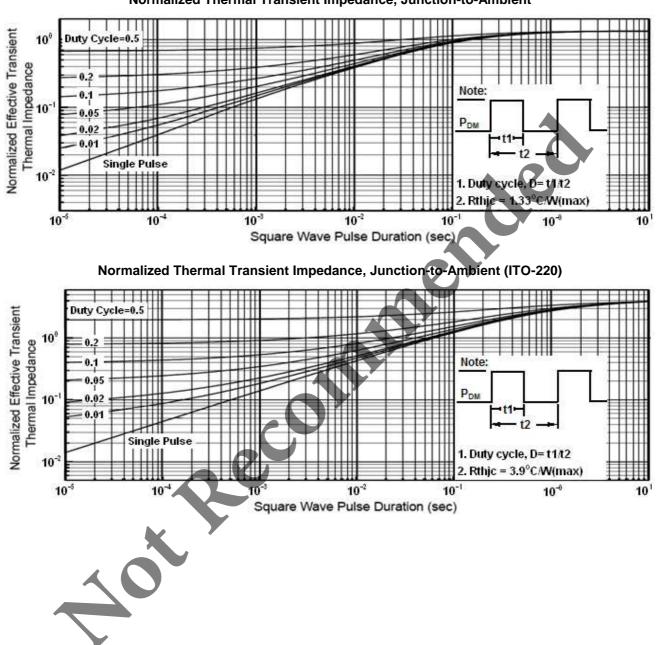


#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



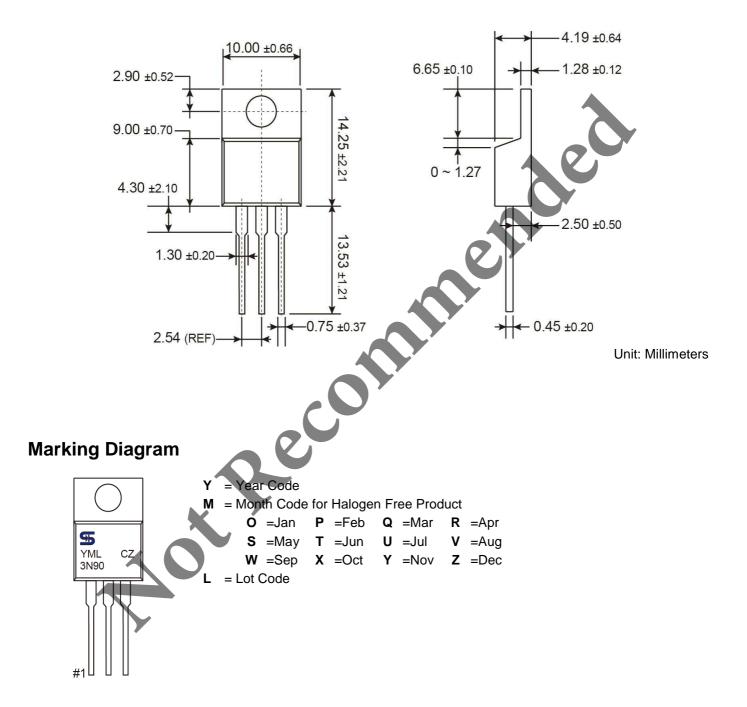


#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



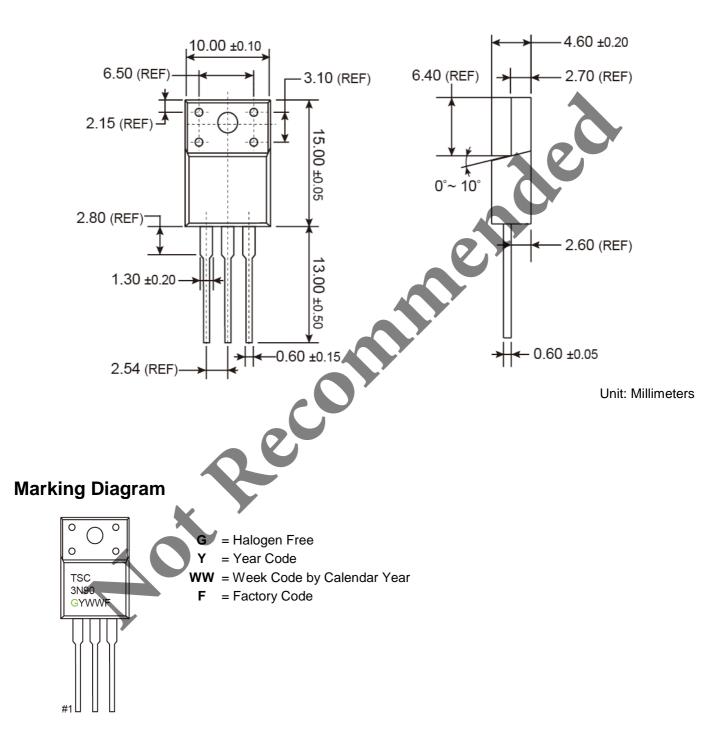


#### **TO-220 Mechanical Drawing**



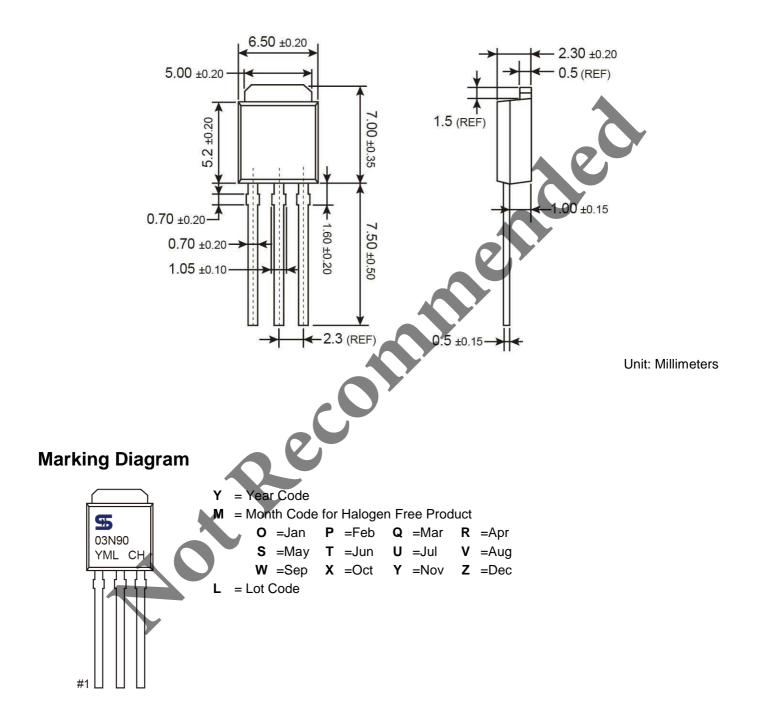


#### **ITO-220 Mechanical Drawing**



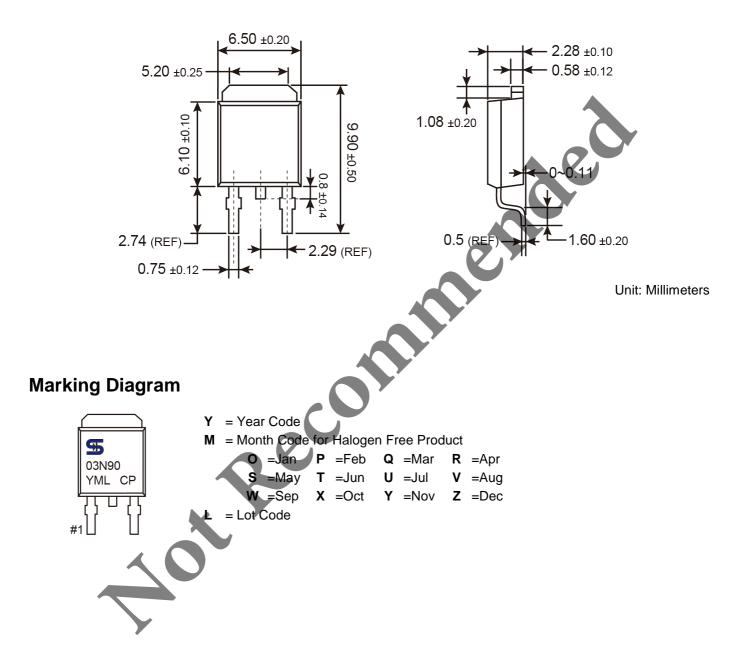


### **TO-251 Mechanical Drawing**

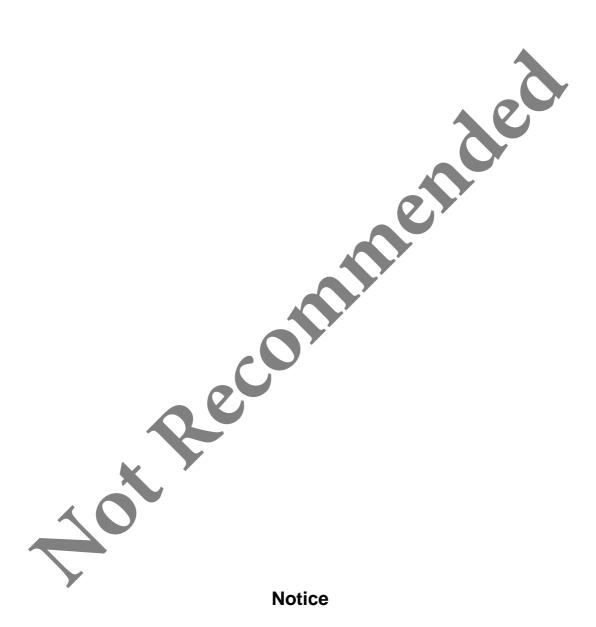




#### **TO-252 Mechanical Drawing**







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